

Phase Control Thyristors (Stud Version), 330 A



TO-118 (TO- 209AE)

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	330 A
V_{DRM}/V_{RRM}	400 V, 800 V, 1200 V, 1400 V, 1600 V, 2000 V
V_{TM}	1.52 V
I_{GT}	200 mA
T_J	-40 °C to +125 °C
Package	TO-118 (TO-209AE)
Circuit configuration	Single SCR

FEATURES

- Center amplifying gate
- International standard case TO-118 (TO-209AE)
- Hermetic metal case with ceramic insulator
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		330	A
	T_C	75	°C
$I_{T(RMS)}$		520	
I_{TSM}	50 Hz	9000	A
	60 Hz	9420	
I^2t	50 Hz	405	KA^2s
	60 Hz	370	
V_{DRM}/V_{RRM}		400 to 2000	V
t_q	Typical	100	μs
T_J		-40 to +125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST330S	04	400	500	50
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	
	20	2000	2100	

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS	
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave			330	A	
					75	°C	
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 75 °C case temperature			520	A	
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	$t = 10 \text{ ms}$	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	9000		
		$t = 8.3 \text{ ms}$	9420				
		$t = 10 \text{ ms}$	100 % V_{RRM} reapplied		7570		
		$t = 8.3 \text{ ms}$	7920				
Maximum I^2t for fusing	I^2t	$t = 10 \text{ ms}$	No voltage reapplied		405	kA ² s	
		$t = 8.3 \text{ ms}$	370				
		$t = 10 \text{ ms}$	100 % V_{RRM} reapplied		287		
		$t = 8.3 \text{ ms}$	262				
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1 \text{ to } 10 \text{ ms}$, no voltage reapplied			4050	kA ² √s	
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum			0.834	V	
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum			0.898		
Low level value of on-state slope resistance	r_{t1}	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum			0.687	mΩ	
High level value of on-state slope resistance	r_{t2}	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum			0.636		
Maximum on-state voltage	V_{TM}	$I_{pk} = 1000 \text{ A}$, $T_J = T_J$ maximum, $t_p = 10 \text{ ms}$ sine pulse			1.52	V	
Maximum holding current	I_H	$T_J = 25 \text{ °C}$, anode supply 12 V resistive load			600	mA	
Typical latching current	I_L				1000		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1 \mu\text{s}$ $T_J = T_J$ maximum, anode voltage $\leq 80 \% V_{DRM}$			1000	A/μs
Typical delay time	t_d	Gate current A, $dl_g/dt = 1 \text{ A}/\mu\text{s}$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 \text{ °C}$			1.0	μs
Typical turn-off time	t_q	$I_{TM} = 550 \text{ A}$, $T_J = T_J$ maximum, $dl/dt = 40 \text{ A}/\mu\text{s}$, $V_R = 50 \text{ V}$, $dV/dt = 20 \text{ V}/\mu\text{s}$, gate 0 V 100 Ω, $t_p = 500 \mu\text{s}$			100	

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}			500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied			50	mA

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
		TYP.	MAX.		
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		10.0	W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$		2.0	
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0	A
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		20	V
Maximum peak negative gate voltage	$-V_{GM}$			5.0	
DC gate current required to trigger	I_{GT}	$T_J = -40$ °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	200	mA
		$T_J = 25$ °C		100	
		$T_J = 125$ °C		50	
DC gate voltage required to trigger	V_{GT}	$T_J = -40$ °C	12 V anode to cathode applied	2.5	V
		$T_J = 25$ °C		1.8	
		$T_J = 125$ °C		1.1	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated $V_{D(RM)}$ anode to cathode applied	10	mA
DC gate voltage not to trigger	V_{GD}			0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum operating junction temperature range	T_J			-40 to +125	°C
Maximum storage temperature range	T_{Stg}			-40 to +150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation		0.10	K/W
Maximum thermal resistance, case to heatsink	R_{thC-hs}	Mounting surface, smooth, flat and greased		0.03	
Mounting torque, ± 10 %		Non-lubricated threads		48.5 (425)	N · m (lbf · in)
Approximate weight				535	g
Case style		See dimension - link at the end of datasheet		TO-118 (TO-209AE)	

ΔR_{thJC} CONDUCTION					
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS		UNITS
180°	0.011	0.008	$T_J = T_J$ maximum	K/W	
120°	0.013	0.014			
90°	0.017	0.018			
60°	0.025	0.026			
30°	0.041	0.042			

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

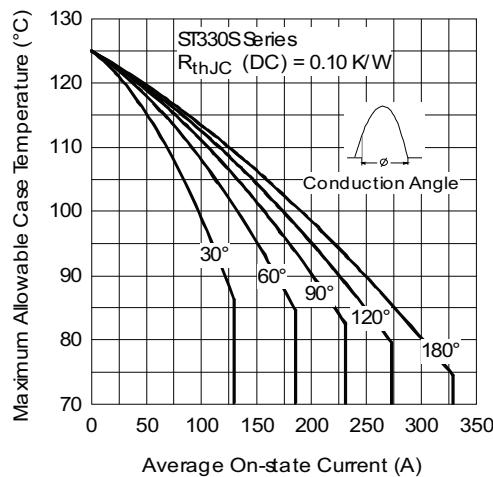


Fig. 1 - Current Ratings Characteristics

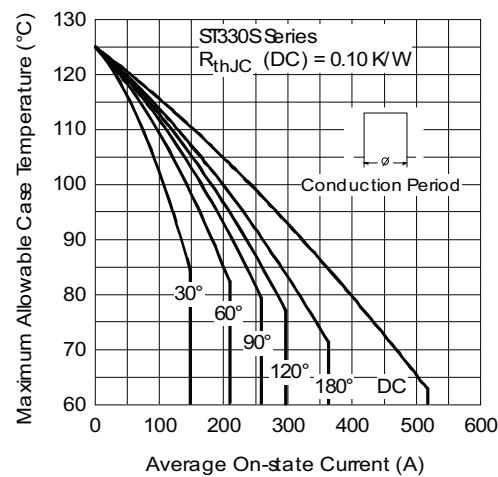


Fig. 2 - Current Ratings Characteristics

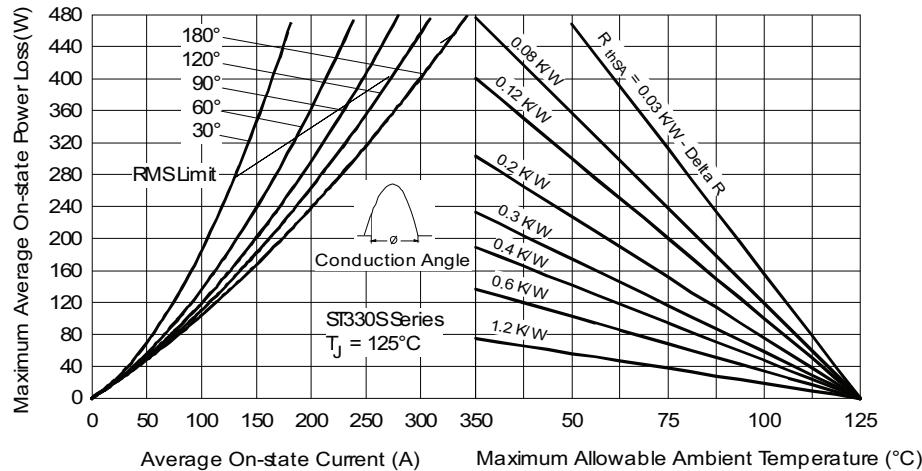


Fig. 3 - On-State Power Loss Characteristics

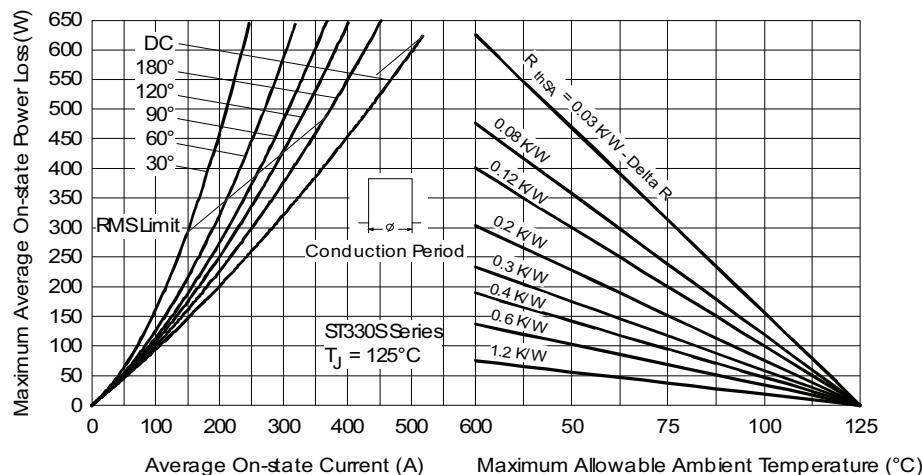


Fig. 4 - On-State Power Loss Characteristics

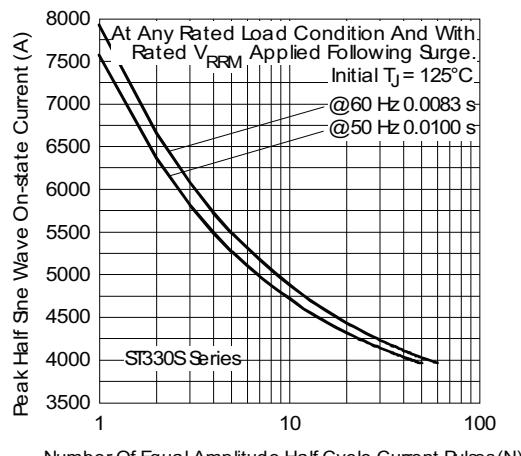


Fig. 5 - Maximum Non-Repetitive Surge Current

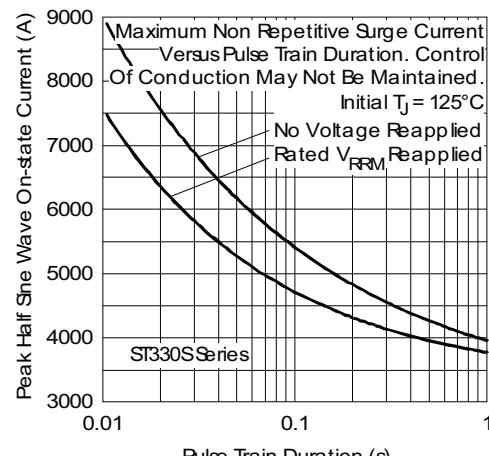


Fig. 6 - Maximum Non-Repetitive Surge Current

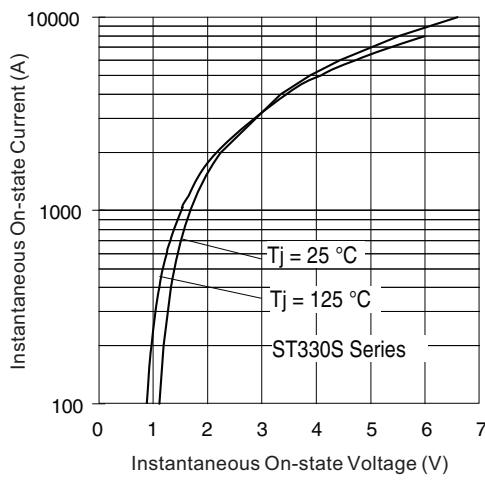


Fig. 7 - On-State Voltage Drop Characteristics

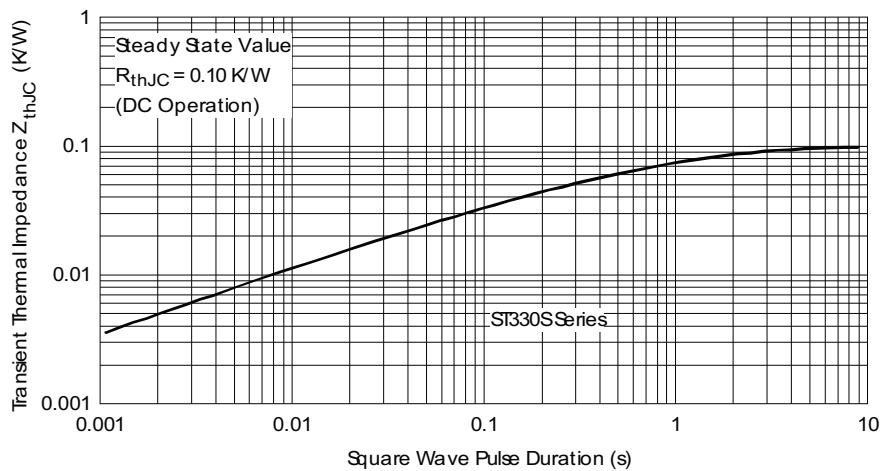


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

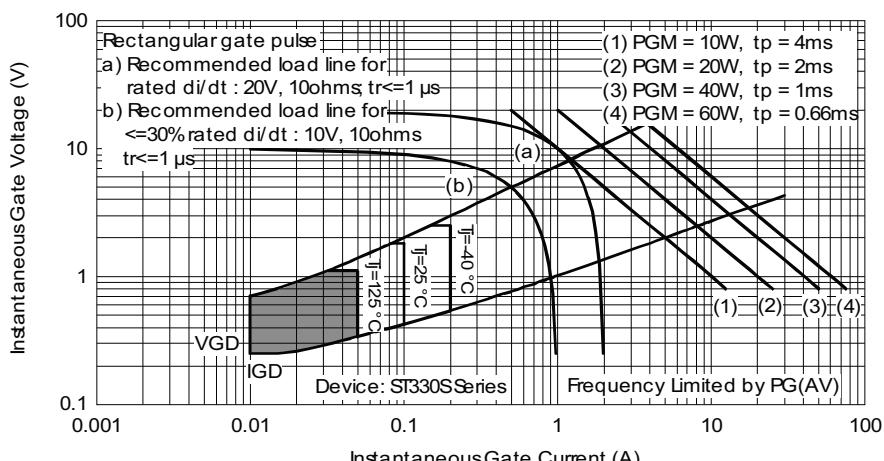


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	33	0	S	16	P	0	PbF
	(1)	(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)

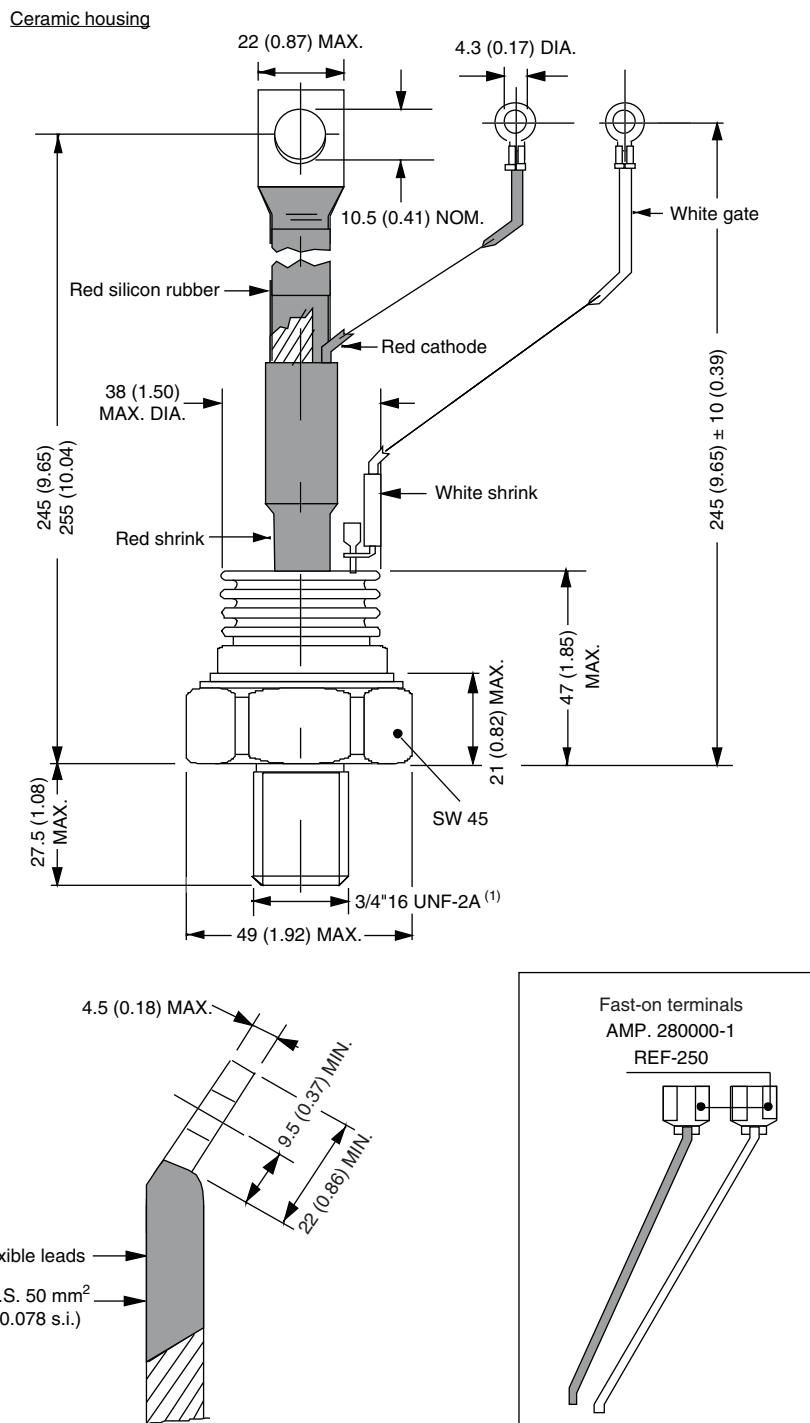
- 1 - Vishay Semiconductors product
- 2 - Thyristor
- 3 - Essential part number
- 4 - 0 = converter grade
- 5 - S = compression bonding stud
- 6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7 - P = stud base 3/4"-16UNF-2A threads
M = stud base metric threads (M24 x 1.5)
- 8 - 0 = eyelet terminals (gate and auxiliary cathode leads)
1 = fast-on terminals (gate and auxiliary cathode leads)
- 9 - None = standard production
- PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95080



TO-209AE (TO-118)

DIMENSIONS in millimeters (inches)



Note

⁽¹⁾ For metric device: M24 x 1.5 - length 21 (0.83) maximum

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.